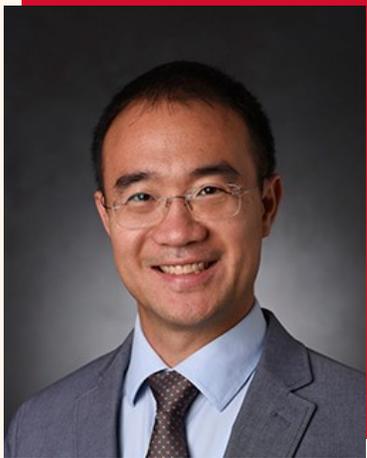


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## Electro-Thermal Analysis of Ultra-Wide Bandgap (UWBG) Electronics

### ABSTRACT:

To extend further the electrical performance envelope of wide bandgap (WBG) power and radio frequency (RF) electronics based on gallium nitride (GaN) and silicon carbide (SiC), device engineers are actively pursuing the development of generation-after-next ultra-wide bandgap (UWBG) devices. At the time being, aluminum gallium nitride (AlGaN),  $\beta$ -gallium oxide (Ga<sub>2</sub>O<sub>3</sub>), and diamond are technologically relevant UWBG materials that have bandgaps larger than that for GaN (3.4 eV). While UWBG devices are built to operate under higher power densities compared to current state-of-the-art WBG counterparts, the thermal conductivities of AlGaN and Ga<sub>2</sub>O<sub>3</sub> are lower than those for GaN and SiC by an order of magnitude. Therefore, self-heating is a major challenge for these UWBG devices. Electro-thermal interactions that lead to self-heating in AlGaN and Ga<sub>2</sub>O<sub>3</sub> devices need to be accurately assessed and understood to accomplish the successful transition from WBG devices to the UWBG technology. In the distinguished departmental seminar, the use of an integrated optical thermography scheme (Raman thermometry, thermoreflectance imaging, and infrared thermography) to study the steady-state and transient thermal characteristics of state-of-the-art UWBG devices will be demonstrated. Tested device technologies include AlGaN-channel high electron mobility transistors (HEMT), Ga<sub>2</sub>O<sub>3</sub> Schottky Barrier Diodes (SBD), lateral Ga<sub>2</sub>O<sub>3</sub> metal-oxide-semiconductor field-effect transistors (MOSFET), and hydrogen (H)-terminated diamond FETs. Results are validated through the use of coupled electro-thermal modeling. In addition, we will report our recent progress on the development of new optical temperature and stress metrology techniques suitable for UWBG electronics including "2-D transducer-assisted Raman thermography."



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